

# BUT32 Transistor Datasheet. Parameters and Characteristics.

Name: BUT32

Material of transistor: Si

Polarity: npn

Maximum collector power dissipation ( $P_c$ ): 250W

Maximum collector-base voltage ( $U_{cb}$ ): 400V

Maximum collector-emitter voltage ( $U_{ce}$ ): 300V

Maximum emitter-base voltage ( $U_{eb}$ ): -

Maximum collector current ( $I_c$  max): 80A

Maximum junction temperature ( $T_j$ ): 200°C

Transition frequency ( $f_t$ ): -

Collector capacitance ( $C_c$ ), P<sub>f</sub>: -

Forward current transfer ratio ( $h_{FE}$ ), min/max: 25T

Manufacturer of BUT32 transistor: STE

Package of BUT32 transistor: TO66

Application: Power, Switching